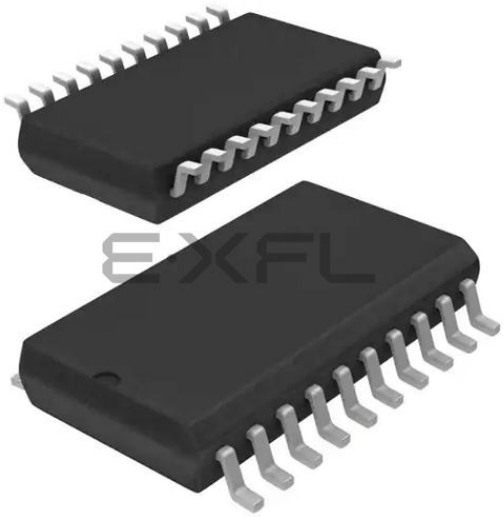

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	STM8
Core Size	8-Bit
Speed	16MHz
Connectivity	I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, POR, PWM, WDT
Number of I/O	16
Program Memory Size	8KB (8K x 8)
Program Memory Type	FLASH
EEPROM Size	640 x 8
RAM Size	1K x 8
Voltage - Supply (Vcc/Vdd)	2.95V ~ 5.5V
Data Converters	A/D 5x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	20-SOIC (0.295", 7.50mm Width)
Supplier Device Package	20-SO
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm8s103f3m6

List of figures

1 Introduction

This datasheet contains the description of the device features, pinout, electrical characteristics, mechanical data and ordering information.

- For complete information on the STM8S microcontroller memory, registers and peripherals, please refer to the STM8S microcontroller family reference manual (RM0016).
- For information on programming, erasing and protection of the internal Flash memory please refer to the STM8S Flash programming manual (PM0051).
- For information on the debug and SWIM (single wire interface module) refer to the STM8 SWIM communication protocol and debug module user manual (UM0470).
- For information on the STM8 core, please refer to the STM8 CPU programming manual (PM0044).

2 Description

The STM8S103F2/x3 access line 8-bit microcontrollers offer 8 Kbyte Flash program memory, plus integrated true data EEPROM. The STM8S microcontroller family reference manual (RM0016) refers to devices in this family as low-density. They provide the following benefits: performance, robustness, and reduced system cost.

Device performance and robustness are ensured by advanced core and peripherals made in a state-of-the art technology, a 16 MHz clock frequency, robust I/Os, independent watchdogs with separate clock source, and a clock security system.

The system cost is reduced thanks to an integrated true data EEPROM for up to 300 k write/erase cycles and a high system integration level with internal clock oscillators, watchdog and brown-out reset.

Full documentation is offered as well as a wide choice of development tools.

Table 1. STM8S103F2/x3 access line features

Device	STM8S103K3	STM8S103F3	STM8S103F2
Pin count	32	20	20
Maximum number of GPIOs (I/Os)	28	16	16
Ext. interrupt pins	27	16	16
Timer CAPCOM channels	7	7	7
Timer complementary outputs	3	2	2
A/D converter channels	4	5	5
High sink I/Os	21	12	12
Low density Flash program memory (bytes)	8K	8K	4K
Data EEPROM (bytes)	640(1)	640(1)	640(1)
RAM (bytes)	1K	1K	1K
Peripheral set	Multipurpose timer (TIM1), SPI, I2C, UART window WDG, independent WDG, ADC, PWM timer (TIM2), 8-bit timer (TIM4)		

1. No read-while-write (RWW) capability.

4.2 Single wire interface module (SWIM) and debug module (DM)

The single wire interface module and debug module permits non-intrusive, real-time in-circuit debugging and fast memory programming.

SWIM

Single wire interface module for direct access to the debug module and memory programming. The interface can be activated in all device operation modes. The maximum data transmission speed is 145 bytes/ms.

Debug module

The non-intrusive debugging module features a performance close to a full-featured emulator. Beside memory and peripherals, also CPU operation can be monitored in real-time by means of shadow registers.

- R/W to RAM and peripheral registers in real-time
- R/W access to all resources by stalling the CPU
- Breakpoints on all program-memory instructions (software breakpoints)
- Two advanced breakpoints, 23 predefined configurations

4.3 Interrupt controller

- Nested interrupts with three software priority levels,
- 32 interrupt vectors with hardware priority,
- Up to 27 external interrupts on 6 vectors including TLI,
- Trap and reset interrupts

4.4 Flash program and data EEPROM memory

- 8 Kbyte of Flash program single voltage Flash memory,
- 640 byte true data EEPROM,
- User option byte area.

Write protection (WP)

Write protection of Flash program memory and data EEPROM is provided to avoid unintentional overwriting of memory that could result from a user software malfunction.

There are two levels of write protection. The first level is known as MASS (memory access security system). MASS is always enabled and protects the main Flash program memory, data EEPROM and option bytes.

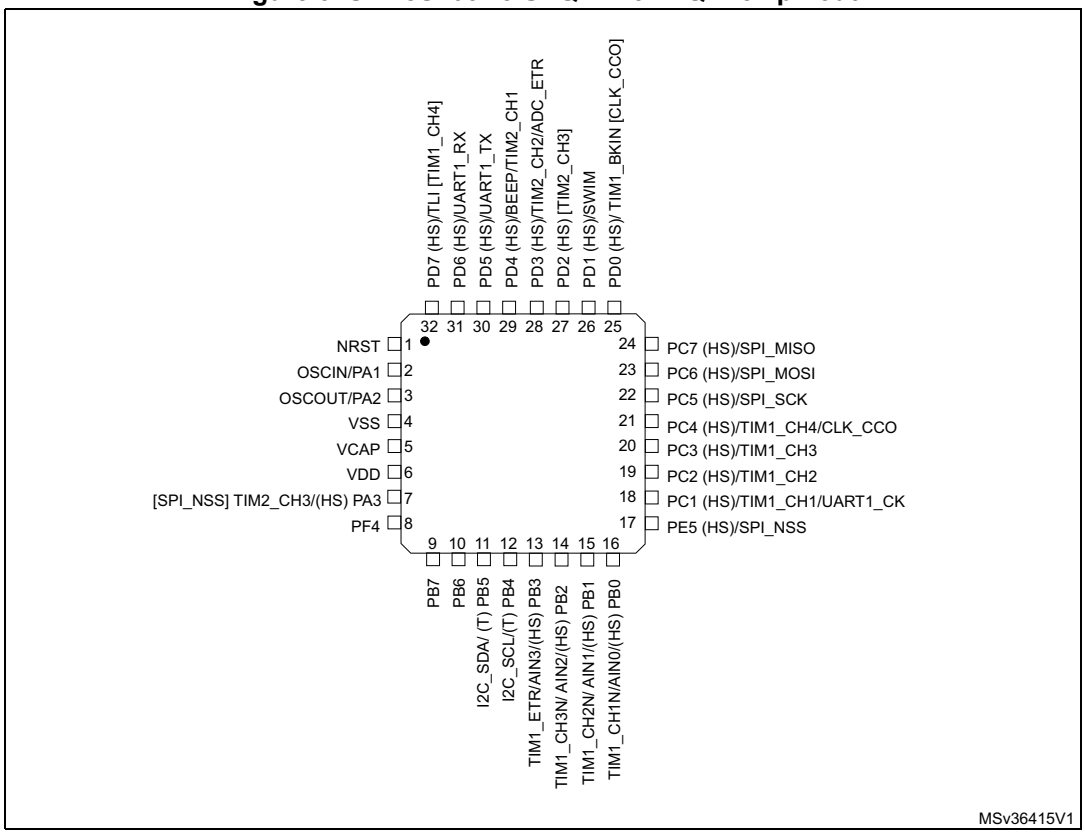
To perform in-application programming (IAP), this write protection can be removed by writing a MASS key sequence in a control register. This allows the application to write to data EEPROM, modify the contents of main program memory or the device option bytes.

A second level of write protection, can be enabled to further protect a specific area of memory known as UBC (user boot code). Refer to the figure below.

The size of the UBC is programmable through the UBC option byte, in increments of 1 page (64-byte block) by programming the UBC option byte in ICP mode.

5.1 STM8S103K3 UFQFPN32/LQFP32/SDIP32 pinout and pin description

Figure 3. STM8S103K3 UFQFPN32/LQFP32 pinout



1. (HS) high sink capability.
2. (T) True open drain (P-buffer and protection diode to V_{DD} not implemented).
3. [ ] alternate function remapping option (if the same alternate function is shown twice, it indicates an exclusive choice not a duplication of the function).

Table 12. Option byte description (continued)

Option byte no.	Description
OPT4	**EXTCLK:** External clock selection 0: External crystal connected to OSCIN/OSCOUT 1: External clock signal on OSCIN
	CKAWUSEL: Auto wake-up unit/clock 0: LSI clock source selected for AWU 1: HSE clock with prescaler selected as clock source for AWU
	PRSC[1:0] AWU clock prescaler 0x: 16 MHz to 128 kHz prescaler 10: 8 MHz to 128 kHz prescaler 11: 4 MHz to 128 kHz prescaler
OPT5	**HSECNT[7:0]:** HSE crystal oscillator stabilization time 0x00: 2048 HSE cycles 0xB4: 128 HSE cycles 0xD2: 8 HSE cycles 0xE1: 0.5 HSE cycles

8.1 Alternate function remapping bits

Table 13. STM8S103K3 alternate function remapping bits for 32-pin devices

Option byte no.	Description(1)
OPT2	**AFR7** Alternate function remapping option 7 Reserved.
	AFR6 Alternate function remapping option 6 0: AFR6 remapping option inactive: Default alternate function.(2) 1: Port D7 alternate function = TIM1_CH4.
	AFR5 Alternate function remapping option 5 0: AFR5 remapping option inactive: Default alternate function.(2) 1: Port D0 alternate function = CLK_CCO.
	AFR[4:2] Alternate function remapping options 4:2 Reserved.
	AFR1 Alternate function remapping option 1 0: AFR1 remapping option inactive: Default alternate functions.(2) 1: Port A3 alternate function = SPI_NSS; port D2 alternate function = TIM2_CH3.
	AFR0 Alternate function remapping option 0 Reserved.

1. Do not use more than one remapping option in the same port. It is forbidden to enable both AFR1 and AFR0.
2. Refer to pinout description.

Table 14. STM8S103Fx alternate function remapping bits for 20-pin devices

Option byte no.	Description
OPT2	**AFR7** Alternate function remapping option 7 0: AFR7 remapping option inactive: Default alternate functions.(1) 1: Port C3 alternate function = TIM1_CH1N; port C4 alternate function = TIM1_CH2N.
	AFR6 Alternate function remapping option 6 Reserved.
	AFR5 Alternate function remapping option 5 Reserved.
	AFR4 Alternate function remapping options 4:2 0: AFR4 remapping option inactive: Default alternate functions.(1) 1: Port B4 alternate function = ADC_ETR; port B5 alternate function = TIM1_BKIN.
	AFR3 Alternate function remapping option 3 0: AFR3 remapping option inactive: Default alternate function.(1) 1: Port C3 alternate function = TLI.
	AFR2 Alternate function remapping option 2 Reserved
	AFR1 Alternate function remapping option 1(2) 0: AFR1 remapping option inactive: Default alternate functions.(1) 1: Port A3 alternate function = SPI_NSS; port D2 alternate function = TIM2_CH3.
	AFR0 Alternate function remapping option 0 0: AFR0 remapping option inactive: Default alternate functions.(1) 1: Port C5 alternate function = TIM2_CH1; port C6 alternate function = TIM1_CH1; port C7 alternate function = TIM1_CH2.

1. Refer to pinout description.
2. Do not use more than one remapping option in the same port. It is forbidden to enable both AFR1 and AFR0.

9 Unique ID

The devices feature a 96-bit unique device identifier which provides a reference number that is unique for any device and in any context. The 96 bits of the identifier can never be altered by the user.

The unique device identifier can be read in single byte and may then be concatenated using a custom algorithm.

The unique device identifier is ideally suited:

- For use as serial numbers
- For use as security keys to increase the code security in the program memory while using and combining this unique ID with software cryptographic primitives and protocols before programming the internal memory.
- To activate secure boot processes

Table 15. Unique ID registers (96 bits)

Address	Content description	Unique ID bits							
		7	6	5	4	3	2	1	0
0x4865	X co-ordinate on the wafer	U_ID[7:0]							
0x4866		U_ID[15:8]							
0x4867	Y co-ordinate on the wafer	U_ID[23:16]							
0x4868		U_ID[31:24]							
0x4869	Wafer number	U_ID[39:32]							
0x486A	Lot number	U_ID[47:40]							
0x486B		U_ID[55:48]							
0x486C		U_ID[63:56]							
0x486D		U_ID[71:64]							
0x486E		U_ID[79:72]							
0x486F		U_ID[87:80]							
0x4870		U_ID[95:88]							

Total current consumption in active halt mode

Table 25. Total current consumption in active halt mode at V_{DD} = 5 V

Symbol	Parameter	Conditions			Typ	Max at 85 °C(1)	Max at 85 °C(1)	Unit
		Main voltage regulator (MVR)(2)	Flash mode(3)	Clock source				
$I_{DD(AH)}$	Supply current in active halt mode	On	Operating mode	HSE crystal osc. (16 MHz)	1030	-	-	µA
			Operating mode	LSI RC osc. (128 kHz)	200	260	300	
			Power down mode	HSE crystal osc. (16 MHz)	970	-	-	
			Power down mode	LSI RC osc. (128 kHz)	150	200	230	
		Off	Operating mode	LSI RC osc. (128 kHz)	66	85	110	
			Power down mode	LSI RC osc. (128 kHz)	10	20	40	

1. Guaranteed by characterization results.
2. Configured by the REGAH bit in the CLK_ICKR register.
3. Configured by the AHALT bit in the FLASH_CR1 register.

Table 26. Total current consumption in active halt mode at V_{DD} = 3.3 V

Symbol	Parameter	Conditions			Typ	Max at 85 °C(1)	Max at 85 °C(1)	Unit
		Main voltage regulator (MVR)(2)	Flash mode(3)	Clock source				
$I_{DD(AH)}$	Supply current in active halt mode	On	Operating mode	HSE crystal osc. (16 MHz)	550	-	-	µA
			Operating mode	LSI RC osc. (128 kHz)	200	260	290	
			Power down mode	HSE crystal osc. (16 MHz)	970	-	-	
			Power down mode	LSI RC osc. (128 kHz)	150	200	230	
		Off	Operating mode	LSI RC osc. (128 kHz)	66	80	105	
			Power down mode	LSI RC osc. (128 kHz)	10	18	35	

1. Guaranteed by characterization results.
2. Configured by the REGAH bit in the CLK_ICKR register.
3. Configured by the AHALT bit in the FLASH_CR1 register.

10.3.3 External clock sources and timing characteristics

HSE user external clock

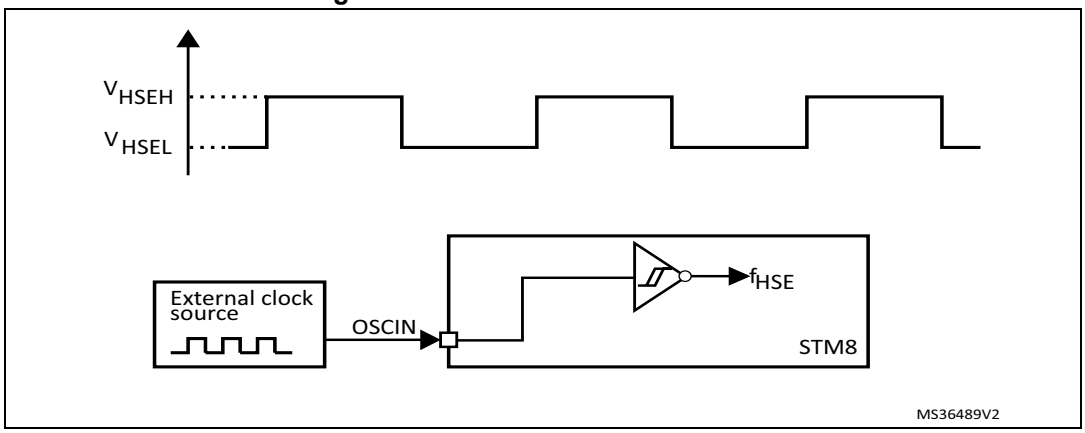
Subject to general operating conditions for V_{DD} and T_A.

Table 32. HSE user external clock characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
f_{HSE_ext}	User external clock source frequency	-	0	16	MHz
V_{HSEH}(1)	OSCIN input pin high level voltage	-	0.7 x V_{DD}	V_{DD} + 0.3 V	V
V_{HSEL}(1)	OSCIN input pin low level voltage	-	V_{SS}	0.3 x V_{DD}	
I_{LEAK_HSE}	OSCIN input leakage current	$V_{SS} < V_{IN} < V_{DD}$	-1	+1	µA

1. Guaranteed by characterization results.

Figure 18. HSE external clock source



10.3.6 I/O port pin characteristics

General characteristics

Subject to general operating conditions for V_{DD} and T_A unless otherwise specified. All unused pins must be kept at a fixed voltage, using the output mode of the I/O for example or an external pull-up or pull-down resistor.

Table 38. I/O static characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{IL}	Input low level voltage	V_{DD} = 5 V	-0.3 V	-	0.3 x V_{DD}	V
V_{IH}	Input high level voltage		0.7 x V_{DD}	-	V_{DD} + 0.3 V	
V_{hys}	Hysteresis(1)		-	700	-	mV
R_{pu}	Pull-up resistor	V_{DD} = 5 V, V_{IN} = V_{SS}	30	55	80	kΩ
t_R, t_F	Rise and fall time (10% - 90%)	Fast I/Os Load = 50 pF	-	-	35(2)	ns
		Standard and high sink I/Os Load = 50 pF	-	-	125(2)	
t_R, t_F	Rise and fall time (10% - 90%)	Fast I/Os Load = 20 pF	-	-	20(2)	ns
		Standard and high sink I/Os Load = 20 pF	-	-	50(2)	
I_{lkg}	Digital input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±1(3)	µA
$I_{lkg\ ana}$	Analog input leakage current	$V_{SS} \leq V_{IN} \leq V_{DD}$	-	-	±250(3)	nA
$I_{lkg(inj)}$	Leakage current in adjacent I/O	Injection current ±4 mA	-	-	±1(3)	µA

1. Hysteresis voltage between Schmitt trigger switching levels. Based on characterization results, not tested in production.
2. Data guaranteed by design.
3. Guaranteed by characterization results

Table 43. SPI characteristics (continued)

Symbol	Parameter	Conditions[1]	Min	Max	Unit
$t_{r(SCK)}$ $t_{f(SCK)}$	SPI clock rise and fall time	Capacitive load: C = 30 pF	-	25	ns
$t_{su(NSS)}$[2]	NSS setup time	Slave mode	4 * t_{MASTER}	-	
$t_{h(NSS)}$[2]	NSS hold time	Slave mode	70	-	
$t_{w(SCKH)}$[2] $t_{w(SCKL)}$[2]	SCK high and low time	Master mode	$t_{SCK}/2$ - 15	$t_{SCK}/2$ + 15	
$t_{su(MI)}$[2] $t_{su(SI)}$[2]	Data input setup time	Master mode	5	-	
		Slave mode	5	-	
$t_{h(MI)}$[2] $t_{h(SI)}$[2]	Data input hold time	Master mode	7	-	
		Slave mode	10	-	
$t_{a(SO)}$[2][3]	Data output access time	Slave mode	-	3* t_{MASTER}	
$t_{dis(SO)}$[2][4]	Data output disable time	Slave mode	25	-	
$t_{v(SO)}$[2]	Data output valid time	Slave mode (after enable edge)	-	65	
$t_{v(MO)}$[2]	Data output valid time	Master mode (after enable edge)	-	30	
$t_{h(SO)}$[2]	Data output hold time	Slave mode (after enable edge)	27	-	
$t_{h(MO)}$[2]		Master mode (after enable edge)	11	-	

1. Parameters are given by selecting 10 MHz I/O output frequency.
2. Values based on design simulation and/or characterization results, and not tested in production.
3. Min time is for the minimum time to drive the output and the max time is for the maximum time to validate the data.
4. Min time is for the minimum time to invalidate the output and the max time is for the maximum time to put the data in Hi-Z.

Electromagnetic interference (EMI)

Based on a simple application running on the product (toggling 2 LEDs through the I/O ports), the product is monitored in terms of emission. This emission test is in line with the norm IEC 61967-2 which specifies the board and the loading of each pin.

Table 49. EMI data

Symbol	Parameter	Conditions				Unit
		General conditions	Monitored frequency band	Max f_{CPU}(1)		
				16 MHz/ 8 MHz	16 MHz/ 16 MHz	
S_{EMI}	Peak level	V_{DD} = 5 V, T_A = 25 °C, LQFP32 package. Conforming to IEC 61967-2	0.1 MHz to 30 MHz	5	5	dBµV
			30 MHz to 130 MHz	4	5	
			130 MHz to 1 GHz	5	5	
	EMI level		EMI level	2.5	2.5	-

1. Guaranteed by characterization results.

Absolute maximum ratings (electrical sensitivity)

Based on two different tests (ESD, DLU and LU) using specific measurement methods, the product is stressed to determine its performance in terms of electrical sensitivity. For more details, refer to the application note AN1181.

Electrostatic discharge (ESD)

Electrostatic discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts x (n+1) supply pin). One model can be simulated: Human body model. This test conforms to the JESD22-A114A/A115A standard. For more details, refer to the application note AN1181.

Table 50. ESD absolute maximum ratings

Symbol	Ratings	Conditions	Class	Maximum value(1)	Unit
$V_{ESD(HBM)}$	Electrostatic discharge voltage (Human body model)	T_A = 25°C, conforming to JESD22-A114	A	4000	V
$V_{ESD(CDM)}$	Electrostatic discharge voltage (Charge device model)	T_A= 25°C, conforming to SD22-C101 LQFP32 package	IV	1000	

1. Guaranteed by characterization results

Static latch-up

Two complementary static tests are required on 10 parts to assess the latch-up performance.

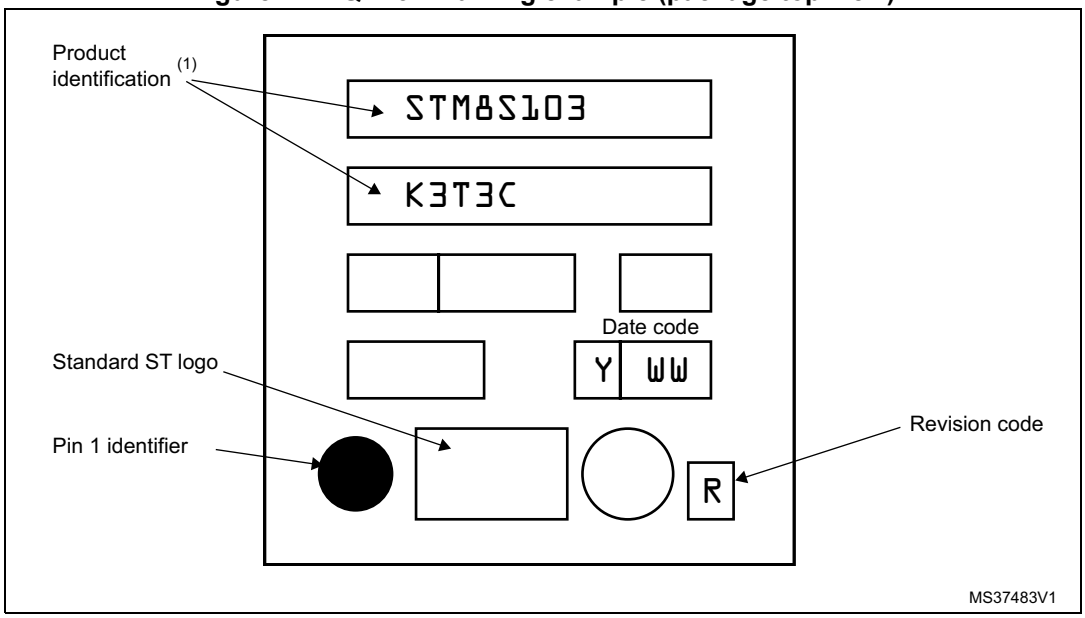
- A supply overvoltage (applied to each power supply pin), and
- A current injection (applied to each input, output and configurable I/O pin) are performed on each sample.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 47. LQFP32 marking example (package top view)



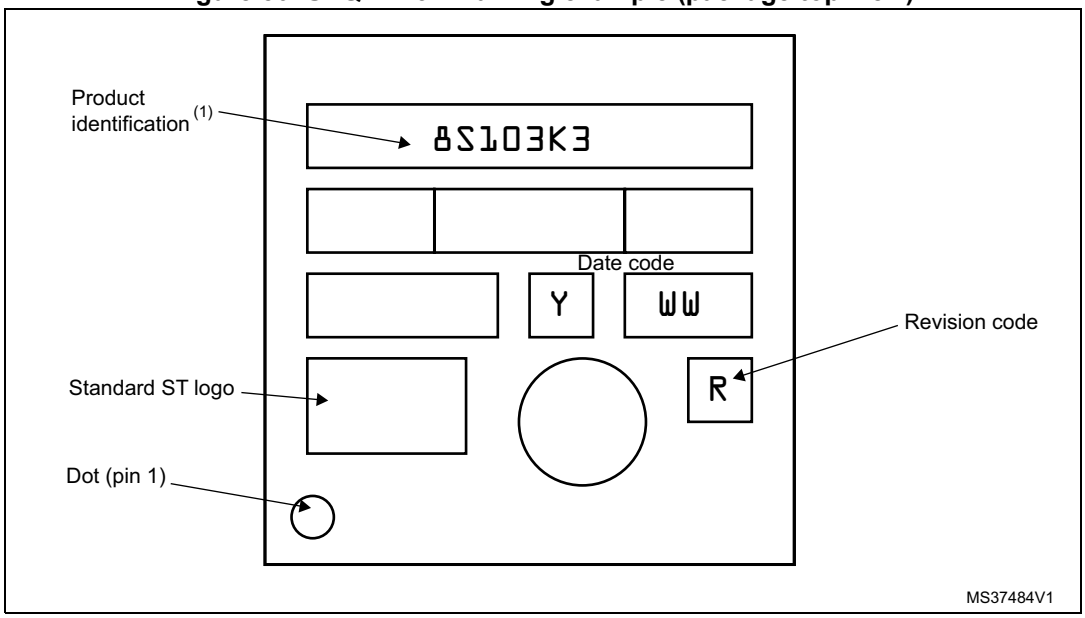
1. Parts marked as “ES”,”E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

Device marking

The following figure gives an example of topside marking orientation versus pin 1 identifier location.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

Figure 50. UFQFPN32 marking example (package top view)



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11.5 TSSOP20 package information

Figure 56. TSSOP20 package outline

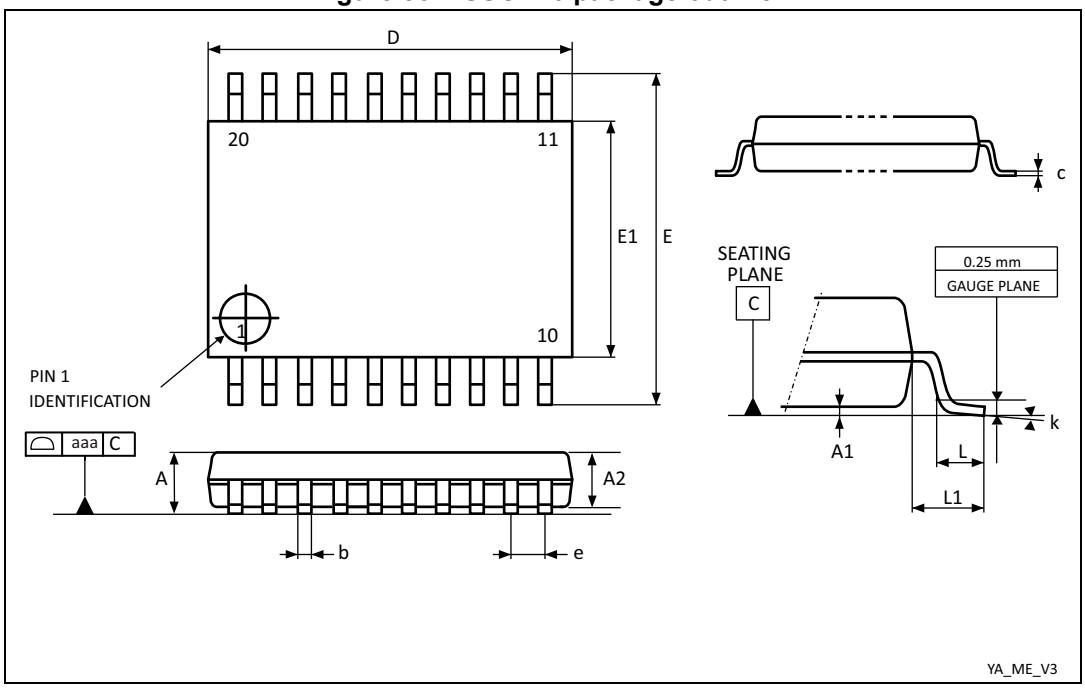


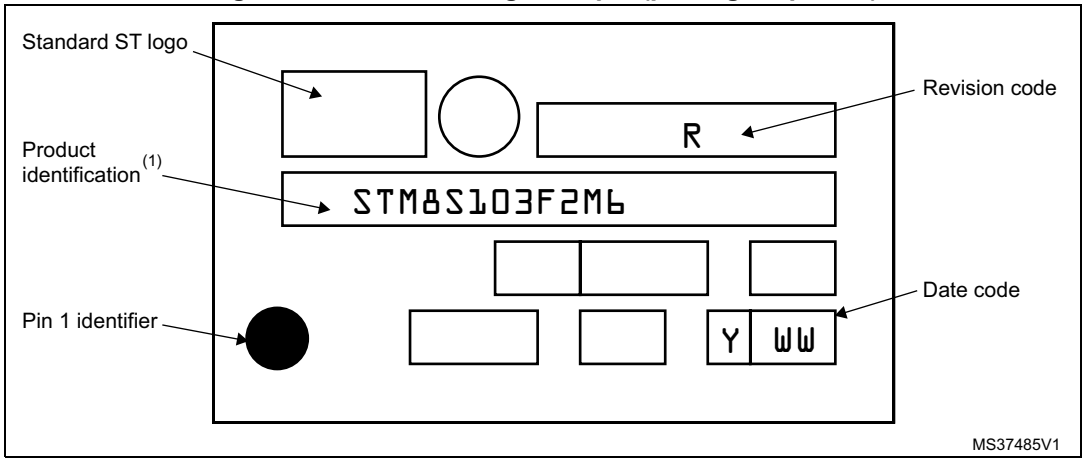
Table 56. TSSOP20 package mechanical data

Dim.	mm			inches(1)		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.200	-	-	0.0472
A1	0.050	-	0.150	0.0020	-	0.0059
A2	0.800	1.000	1.050	0.0315	0.0394	0.0413
b	0.190	-	0.300	0.0075	-	0.0118
c	0.090	-	0.200	0.0035	-	0.0079
D(2)	6.400	6.500	6.600	0.2520	0.2559	0.2598
E	6.200	6.400	6.600	0.2441	0.2520	0.2598
E1(3)	4.300	4.400	4.500	0.1693	0.1732	0.1772
e	-	0.650	-	-	0.0256	-
L	0.450	0.600	0.750	0.0177	0.0236	0.0295
L1	-	1.000	-	-	0.0394	-
k	0.0°	-	8.0°	0.0°	-	8.0°
aaa	-	-	0.100	-	-	0.0039

1. Values in inches are converted from mm and rounded to 4 decimal digits.
2. Dimension “D” does not include mold flash, protrusions or gate burrs. Mold flash, protrusions or gate burrs shall not exceed 0.15mm per side.

Other optional marking or inset/upset marks, which identify the parts throughout supply chain operations, are not indicated below.

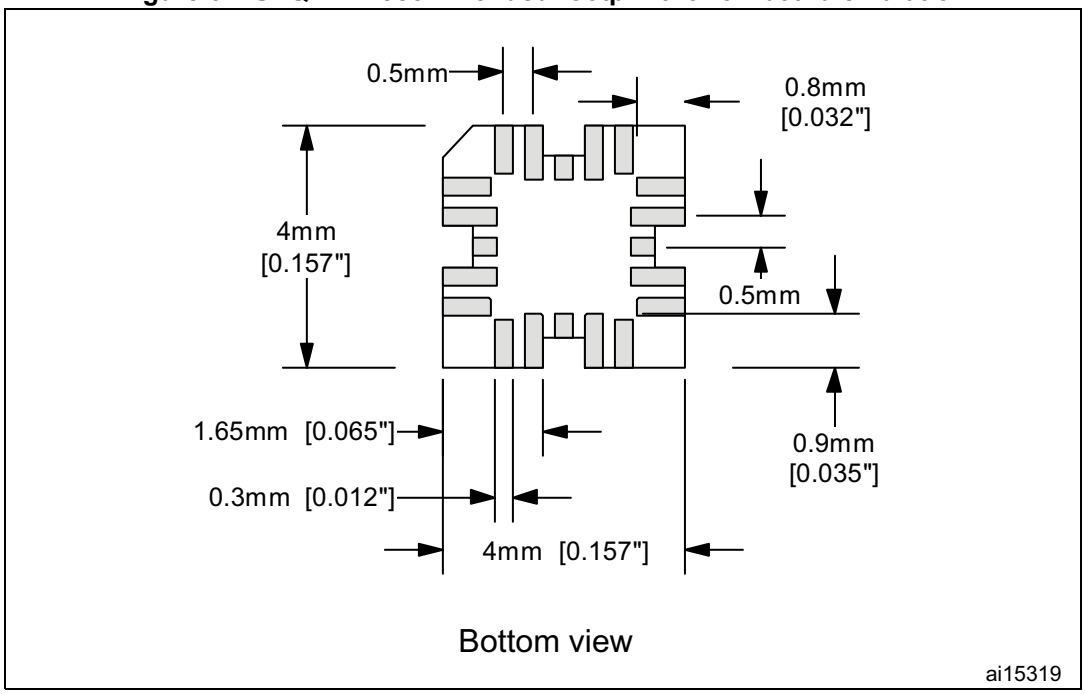
Figure 60. SO20 marking example (package top view)



1. Parts marked as “ES”,”E” or accompanied by an Engineering Sample notification letter, are not yet qualified and therefore not yet ready to be used in production and any consequences deriving from such usage will not be at ST charge. In no event, ST will be liable for any customer usage of these engineering samples in production. ST Quality has to be contacted prior to any decision to use these Engineering samples to run qualification activity.

11.7 UFQFPN recommended footprint

Figure 61. UFQFPN recommended footprint for on-board emulation



15 Revision history

Table 59. Document revision history

Date	Revision	Changes
02-Mar-2009	1	Initial release.
10-Apr-2009	2	Added *Table 2: Peripheral clock gating bit assignments in CLK_PCKENR1/2 registers*. Updated *Section 4.8: Auto wakeup counter*. Modified the description of PB4 and PB5 (removed X in PP column) and added footnote concerning HS I/Os in *Section 5.1: STM8S103K3 UFQFPN32/LQFP32/SDIP32 pinout and pin description* and *Section 5.2: STM8S103F2/F3 TSSOP20/SO20/UFQFPN20 pinout and pin description*. Removed TIM3 and UART from *Table 10: Interrupt mapping*. Updated VCAP specifications in *Section 10.3.1: VCAP external capacitor* Corrected the block size in *Table 37: Flash program memory/data EEPROM memory*t Updated *Section 10: Electrical characteristics*. Updated *Section 12: Thermal characteristics*.
10-Jun-1999	3	Document status changed from “preliminary data” to “datasheet”. Replaced WFQFPN20 package with UFQFPN package. Replaced ‘VFQFN’ with ‘VFQFPN’. Added bullet point on the unique identifier to *Features*. Updated *Section 4.8: Auto wakeup counter*. Updated wpu and PP status of PB5/12C_SDA and PB4/12C_SCL pins in *Section 5.1: STM8S103K3 UFQFPN32/LQFP32/SDIP32 pinout and pin description* and *Section 5.2: STM8S103F2/F3 TSSOP20/SO20/UFQFPN20 pinout and pin description*. Removed Table 7: Pin-to-pin comparison of pin 7 to 12 in 32-pin access line devices. Updated *Section 6.1: Memory map*. Updated reset status of port D CR1 register in *Table 7: I/O port hardware register map*. Updated alternate function remapping descriptions in *Table 13: STM8S103K3 alternate function remapping bits for 32-pin devices* and *Table 14: STM8S103Fx alternate function remapping bits for 20-pin devices*. Added *Section 9: Unique ID*. Updated *Section 10.3: Operating conditions*. Updated the caption of *Figure 20: Typical HSI frequency variation vs V_{DD} @ 4 temperatures*. Updated *Table 43: SPI characteristics* and added TBD occurrences. Added max values to *Table 46: ADC accuracy with R_{AIN}< 10 kΩ V_{DD}= 5 V* and *Table 47: ADC accuracy with R_{AIN}< 10 kΩ V_{DD}= 3.3 V*. Updated *Section 10.3.11: EMC characteristics*.

Table 59. Document revision history

Date	Revision	Changes
04-Apr-2012	8	Updated notes related to V_{CAP} in *Table 19: General operating conditions*. Added values of t_R/t_F for 50 pF load capacitance, and updated note in *Table 38: I/O static characteristics*. Updated typical and maximum values of R_{PU} in *Table 38: I/O static characteristics* and *Table 42: NRST pin characteristics*. Changed SCK input to SCK output in *Section 10.3.8: SPI serial peripheral interface* Modified *Figure 51: UFQFPN20 - 20-lead, 3x3 mm, 0.5 mm pitch, ultra thin fine pitch quad flat package outline* to add package top view.
26-Jun-2012	9	Added *Section 11.4: SDIP32 package information*.
04-Feb-2015	10	Updated *Section 11.5: TSSOP20 package information* and *Section 11.3: UFQFPN20 package information*.
10-Mar-2015	11	Updated: – *Table 34: HSI oscillator characteristics*: corrected HSI oscillator accuracy (factory calibrated) for V_{DD} = 5 V and T_A = 25 °C. – *Table 38: I/O static characteristics*: corrected the max. value for T_R/T_F, Fast I/Os, Load = 50 pF. Added: – *Figure 23: Typical pull-up current vs V_{DD} @ 4 temperatures*, – the rows for T_R/T_F, Fast I/Os, Load = 20 pF in *Table 38: I/O static characteristics*, – *Figure 47: LQFP32 marking example (package top view)*, – *Figure 50: UFQFPN32 marking example (package top view)*, – *Figure 53: UFQFPN20 marking example (package top view)*, – *Figure 55: SDIP32 marking example (package top view)*, – *Figure 58: TSSOP20 marking example (package top view)*, – *Figure 60: SO20 marking example (package top view)*.
26-Mar-2015	12	Corrected the values for “b” dimensions in *Table 53: UFQFPN32 - 32-pin, 5x5 mm, 0.5 mm pitch ultra thin fine pitch quad flat package mechanical data*.